PATENT APPLICATION

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE Application of

Satoshi INOUE Group Art Unit: 2811

Application No.: 10/814,169

Filed: April 1, 2004 Docket No.: 119330

For: METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, INTEGRATED CIRCUIT, ELECTRO-OPTICAL DEVICE, AND ELECTRONIC APPARATUS

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 CFR §1.56, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached PTO-1449. Unless otherwise indicated herein, one copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

- 1. This Information Disclosure Statement is being filed (a) within three months of the U.S. filing date of this non-CPA application, OR (b) before the mailing date of a first Office Action on the merits in the present application. No certification or fee is required.
- 2. Relevance of the non-English language references 1 and 2 are discussed in the present specification.

Respectfully submitted,

James A. Oliff

Registration No. 27,075

Michael Britton

Registration No. 47,260

JAO:MB/can

Date: August 3, 2004

OLIFF & BERRIDGE, PLC P.O. Box 19928 Alexandria, Virginia 22320 Telephone: (703) 836-6400 DEPOSIT ACCOUNT USE
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INFORMATION DISCLOSURE STATEMENT									
(Use several sheets if necessary) AUG 0 3 7004 U.S. PATI		APPLICANT Satoshi INOUE							
		FILING DATE April 1, 2004				GROUP 2811			
U.S. PA	TENT	DOCU	MENTS						
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OTHER DOCUMENTS (Include	ling Au	thor, T	itle, Date, I	Pertinent	t Pages,	etc.)		,]	
1 "Single Crystal Thin Film Transistors", IE									
R. Ishihara et al., "Advanced Excimer-La Grain on Glass", proc. SPIE 2001, Vol. 42	R. Ishihara et al., "Advanced Excimer-Laser Crystallization Techniques of Si Thin-Film For Loacation Control of Large Grain on Glass", proc. SPIE 2001, Vol. 4295, pp. 14-23.								
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Examiner: Initial if citation considered, whether or not citatic conformance and not considered. Include copy of the							line th	rough citati	on if not in

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